List of Publications by Year in descending order

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		76326	33894
192	11,144	40	99
papers	citations	h-index	g-index
192	192	192	7543
all docs	docs citations	times ranked	citing authors

#	Article	IF	CITATIONS
1	High-performance Ge-on-Si photodetectors. Nature Photonics, 2010, 4, 527-534.	31.4	1,215
2	A Dielectric Omnidirectional Reflector. , 1998, 282, 1679-1682.		1,148
3	Ge-on-Si laser operating at room temperature. Optics Letters, 2010, 35, 679.	3.3	818
4	An electrically pumped germanium laser. Optics Express, 2012, 20, 11316.	3.4	689
5	Tensile-strained, n-type Ge as a gain medium for monolithic laser integration on Si. Optics Express, 2007, 15, 11272.	3.4	557
6	Waveguide-integrated, ultralow-energy GeSi electro-absorption modulators. Nature Photonics, 2008, 2, 433-437.	31.4	466
7	High performance, waveguide integrated Ge photodetectors. Optics Express, 2007, 15, 3916.	3.4	426
8	On-chip light sources for silicon photonics. Light: Science and Applications, 2015, 4, e358-e358.	16.6	418
9	Direct gap photoluminescence of n-type tensile-strained Ge-on-Si. Applied Physics Letters, 2009, 95, .	3.3	246
10	Room-temperature direct bandgap electroluminesence from Ge-on-Si light-emitting diodes. Optics Letters, 2009, 34, 1198.	3.3	223
11	Nonlinear Group IV photonics based on silicon and germanium: from near-infrared to mid-infrared. Nanophotonics, 2014, 3, 247-268.	6.0	219
12	High-performance, tensile-strained Ge p-i-n photodetectors on a Si platform. Applied Physics Letters, 2005, 87, 103501.	3.3	205
13	Horizontal single and multiple slot waveguides: optical transmission at λ = 1550 nm. Optics Express, 2007, 15, 17967.	3.4	202
14	Tensile strained Ge p-i-n photodetectors on Si platform for C and L band telecommunications. Applied Physics Letters, 2005, 87, 011110.	3.3	189
15	Deformation potential constants of biaxially tensile stressedGeepitaxial films onSi(100). Physical Review B, 2004, 70, .	3.2	155
16	Demonstration of a Tunable Microwave-Photonic Notch Filter Using Low-Loss Silicon Ring Resonators. Journal of Lightwave Technology, 2009, 27, 2105-2110.	4.6	153
17	Strain-induced enhancement of near-infrared absorption in Ge epitaxial layers grown on Si substrate. Journal of Applied Physics, 2005, 98, 013501.	2.5	148
18	Direct-gap optical gain of Ge on Si at room temperature. Optics Letters, 2009, 34, 1738.	3.3	146

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19	Tensile strained epitaxial Ge films on Si(100) substrates with potential application inL-band telecommunications. Applied Physics Letters, 2004, 84, 906-908.	3.3	141
20	Ge-on-Si optoelectronics. Thin Solid Films, 2012, 520, 3354-3360.	1.8	137
21	Design of Highly Efficient Light-Trapping Structures for Thin-Film Crystalline Silicon Solar Cells. IEEE Transactions on Electron Devices, 2007, 54, 1926-1933.	3.0	133
22	Nonlinear conversion efficiency in Kerr frequency comb generation. Optics Letters, 2014, 39, 6126.	3.3	125
23	Toward a Germanium Laser for Integrated Silicon Photonics. IEEE Journal of Selected Topics in Quantum Electronics, 2010, 16, 124-131.	2.9	122
24	Design of monolithically integrated GeSi electro-absorption modulators and photodetectors on a SOI platform. Optics Express, 2007, 15, 623.	3.4	106
25	Optimization-based design of surface textures for thin-film Si solar cells. Optics Express, 2011, 19, A841.	3.4	104
26	Athermal operation of Silicon waveguides: spectral, second order and footprint dependencies. Optics Express, 2010, 18, 17631.	3.4	101
27	Monolithic Ge-on-Si lasers for large-scale electronic–photonic integration. Semiconductor Science and Technology, 2012, 27, 094006.	2.0	96
28	Impedance matching vertical optical waveguide couplers for dense high index contrast circuits. Optics Express, 2008, 16, 11682.	3.4	91
29	Direct band gap narrowing in highly doped Ge. Applied Physics Letters, 2013, 102, .	3.3	84
30	Lossless strip-to-slot waveguide transformer. Optics Letters, 2007, 32, 1250.	3.3	83
31	Demonstration of a Fourth-Order Pole-Zero Optical Filter Integrated Using CMOS Processes. Journal of Lightwave Technology, 2007, 25, 87-92.	4.6	83
32	Athermal High-Index-Contrast Waveguide Design. IEEE Photonics Technology Letters, 2008, 20, 885-887.	2.5	70
33	Generation of two-cycle pulses and octave-spanning frequency combs in a dispersion-flattened micro-resonator. Optics Letters, 2013, 38, 5122.	3.3	70
34	Large electro-optic effect in tensile strained Ge-on-Si films. Applied Physics Letters, 2006, 89, 161115.	3.3	63
35	Design and Nonâ€Lithographic Fabrication of Light Trapping Structures for Thin Film Silicon Solar Cells. Advanced Materials, 2011, 23, 843-847.	21.0	63
36	Single element spectral splitting solar concentrator for multiple cells CPV system. Optics Express, 2012, 20, 9004.	3.4	62

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37	Silicon RF-Photonic Filter and Down-Converter. Journal of Lightwave Technology, 2010, 28, 3019-3028.	4.6	61
38	High active carrier concentration in n-type, thin film Ge using delta-doping. Optical Materials Express, 2012, 2, 1462.	3.0	55
39	Transparent amorphous silicon channel waveguides with silicon nitride intercladding layer. Applied Physics Letters, 2009, 94, 141108.	3.3	52
40	High-efficiency normal-incidence vertical p-i-n photodetectors on a germanium-on-insulator platform. Photonics Research, 2017, 5, 702.	7.0	52
41	Reduction of threading dislocation density in Ge/Si using a heavily As-doped Ge seed layer. AIP Advances, 2016, 6, .	1.3	47
42	Bilayer dispersion-flattened waveguides with four zero-dispersion wavelengths. Optics Letters, 2016, 41, 4939.	3.3	41
43	Silicidation-induced band gap shrinkage in Ge epitaxial films on Si. Applied Physics Letters, 2004, 84, 660-662.	3.3	40
44	Germanium-rich silicon-germanium films epitaxially grown by ultrahigh vacuum chemical-vapor deposition directly on silicon substrates. Applied Physics Letters, 2007, 91, 252111.	3.3	40
45	Analysis of Threshold Current Behavior for Bulk and Quantum-Well Germanium Laser Structures. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1901009-1901009.	2.9	40
46	Er2O3 for high-gain waveguide amplifiers. Journal of Electronic Materials, 2004, 33, 809-814.	2.2	39
47	Silicon-based highly-efficient fiber-to-waveguide coupler for high index contrast systems. Applied Physics Letters, 2006, 88, 081112.	3.3	39
48	Integration of Self-Assembled Porous Alumina and Distributed Bragg Reflector for Light Trapping in Si Photovoltaic Devices. IEEE Photonics Technology Letters, 2010, 22, 1394-1396.	2.5	39
49	High phosphorous doped germanium: Dopant diffusion and modeling. Journal of Applied Physics, 2012, 112, .	2.5	38
50	Integrated photonic structures for light trapping in thin-film Si solar cells. Applied Physics Letters, 2012, 100, 111110.	3.3	38
51	Graphene-based optical phase modulation of waveguide transverse electric modes. Photonics Research, 2014, 2, A34.	7.0	38
52	Design for energy: Modeling of spectrum, temperature and device structure dependences of solar cell energy production. Solar Energy Materials and Solar Cells, 2015, 136, 48-63.	6.2	38
53	Monitoring and Optimization of Silicon Surface Quality. Journal of the Electrochemical Society, 1995, 142, 2833-2835.	2.9	37
54	Light-Emitting Silicon Nanocrystals and Photonic Structures in Silicon Nitride. IEEE Journal of Selected Topics in Quantum Electronics, 2006, 12, 1628-1635.	2.9	36

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55	Hybrid nano ridge plasmonic polaritons waveguides. Applied Physics Letters, 2013, 103, .	3.3	36
56	Post-fabrication trimming of athermal silicon waveguides. Optics Letters, 2013, 38, 5450.	3.3	34
57	On-Chip Octave-Spanning Supercontinuum in Nanostructured Silicon Waveguides Using Ultralow Pulse Energy. IEEE Journal of Selected Topics in Quantum Electronics, 2012, 18, 1799-1806.	2.9	33
58	Ultra-flat dispersion in an integrated waveguide with five and six zero-dispersion wavelengths for mid-infrared photonics. Photonics Research, 2019, 7, 1279.	7.0	33
59	Robust polarization-insensitive strip-slot waveguide mode converter based on symmetric multimode interference. Optics Express, 2016, 24, 7347.	3.4	32
60	Breaking the Energy-Bandwidth Limit of Electrooptic Modulators: Theory and a Device Proposal. Journal of Lightwave Technology, 2013, 31, 4029-4036.	4.6	30
61	Increased bandwidth with flattened and low dispersion in a horizontal double-slot silicon waveguide. Journal of the Optical Society of America B: Optical Physics, 2015, 32, 26.	2.1	30
62	Mid-IR supercontinuum generated in low-dispersion Ge-on-Si waveguides pumped by sub-ps pulses. Optics Express, 2017, 25, 16116.	3.4	28
63	Large inherent optical gain from the direct gap transition of Ge thin films. Applied Physics Letters, 2013, 102, 131116.	3.3	27
64	Efficient evanescent wave coupling conditions for waveguide-integrated thin-film Si/Ge photodetectors on silicon-on-insulator/germanium-on-insulator substrates. Journal of Applied Physics, 2011, 110, .	2.5	25
65	Infrared absorption of n-type tensile-strained Ge-on-Si. Optics Letters, 2013, 38, 652.	3.3	25
66	Athermal and flat-topped silicon Mach-Zehnder filters. Optics Express, 2016, 24, 29577.	3.4	25
67	Transparent amorphous silicon channel waveguides and high-Q resonators using a damascene process. Optics Letters, 2009, 34, 2378.	3.3	23
68	Light trapping limits in plasmonic solar cells: an analytical investigation. Optics Express, 2012, 20, A496.	3.4	22
69	The Physics and Application of Si:Er for Light Emitting Diodes. Materials Science Forum, 1994, 143-147, 707-714.	0.3	20
70	Singleâ€Crystal Germanium Growth on Amorphous Silicon. Advanced Functional Materials, 2012, 22, 1049-1057.	14.9	20
71	Design and fabrication of a high transmissivity metal-dielectric ultraviolet band-pass filter. Applied Physics Letters, 2013, 102, .	3.3	20
72	Modeling of Aperiodic Fractal Waveguide Structures for Multifrequency Light Transport. Journal of Lightwave Technology, 2007, 25, 1841-1847.	4.6	19

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73	Silicon-on-nitride structures for mid-infrared gap-plasmon waveguiding. Applied Physics Letters, 2014, 104, 031115.	3.3	19
74	Optical Bleaching of Thin Film Ge on Si. ECS Transactions, 2008, 16, 881-889.	0.5	18
75	Broadband athermal waveguides and resonators for datacom and telecom applications. Photonics Research, 2018, 6, 987.	7.0	18
76	Parameter Space Exploration in Dispersion Engineering of Multilayer Silicon Waveguides from Near-Infrared to Mid-Infrared. Journal of Lightwave Technology, 2016, 34, 3696-3702.	4.6	17
77	Stability of polymer-dielectric bi-layers for athermal silicon photonics. Optics Express, 2012, 20, 16059.	3.4	16
78	An Electrically Pumped Ge-on-Si Laser. , 2012, , .		16
79	Loss reduction of silicon-on-insulator waveguides for deep mid-infrared applications. Optics Letters, 2017, 42, 3454.	3.3	16
80	Power-efficient generation of two-octave mid-IR frequency combs in a germanium microresonator. Nanophotonics, 2018, 7, 1461-1467.	6.0	16
81	High performance asymmetric graded index coupler with integrated lens for high index waveguides. Applied Physics Letters, 2007, 90, 201116.	3.3	15
82	Design and fabrication of high-index-contrast self-assembled texture for light extraction enhancement in LEDs. Optics Express, 2011, 19, A701.	3.4	15
83	Hetero-epitaxy of high quality germanium film on silicon substrate for optoelectronic integrated circuit applications. Journal of Materials Research, 2017, 32, 4025-4040.	2.6	15
84	Soliton breathing induced by stimulated Raman scattering and self-steepening in octave-spanning Kerr frequency comb generation. Optics Express, 2015, 23, 18665.	3.4	14
85	Synthesis, Characterization, and Modeling of Nitrogen-Passivated Colloidal and Thin Film Silicon Nanocrystals. IEEE Journal of Selected Topics in Quantum Electronics, 2006, 12, 1151-1163.	2.9	13
86	Towards a Ge-based laser for CMOS applications. , 2008, , .		13
87	Co-polymer clad design for high performance athermal photonic circuits. Optics Express, 2012, 20, 20808.	3.4	13
88	Intra-Cavity Dispersion of Microresonators and its Engineering for Octave-Spanning Kerr Frequency Comb Generation. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 111-117.	2.9	13
89	Ultralow-Power LED-Enabled On-Chip Optical Communication Designed in the III-Nitride and Silicon CMOS Process Integrated Platform. IEEE Design and Test, 2014, 31, 36-45.	1.2	13
90	Chemical Mechanical Polishing of Selective Epitaxial Grown Germanium on Silicon. ECS Journal of Solid State Science and Technology, 2014, 3, P5-P9.	1.8	12

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91	High level active <i>n</i> + doping of strained germanium through co-implantation and nanosecond pulsed laser melting. Journal of Applied Physics, 2018, 123, .	2.5	12
92	An Electrically Pumped Ge-on-Si Laser. , 2012, , .		12
93	Towards ultra-subwavelength optical latches. Applied Physics Letters, 2013, 103, .	3.3	11
94	Linear-regression-based approach for loss extraction from ring resonators. Optics Letters, 2016, 41, 4747.	3.3	11
95	Sub-mA/cm <sup>2</sup> Dark Current Density, Buffer-Less Germanium (Ge) Photodiodes on a 200-mm Ge-on-Insulator Substrate. IEEE Transactions on Electron Devices, 2021, 68, 1730-1737.	3.0	10
96	Ultralow energy, integrated GeSi electroabsorption modulators on SOI. , 2008, , .		9
97	Robust cavity soliton formation with hybrid dispersion. Photonics Research, 2018, 6, 647.	7.0	9
98	High-performance AlGaInP light-emitting diodes integrated on silicon through a superior quality germanium-on-insulator. Photonics Research, 2018, 6, 290.	7.0	8
99	Effectiveness of InGaAs/GaAs superlattice dislocation filter layers epitaxially grown on 200 mm Si wafers with and without Ge buffers. Semiconductor Science and Technology, 2020, 35, 095036.	2.0	8
100	Coupling efficiency of monolithic, waveguide-integrated Si photodetectors. Applied Physics Letters, 2009, 94, 081108.	3.3	7
101	Strategies for increased donor electrical activity in germanium (opto-) electronic materials: a review. International Materials Reviews, 2017, 62, 334-347.	19.3	7
102	Compact spectrum splitter for laterally arrayed multi-junction concentrator photovoltaic modules. Optics Letters, 2019, 44, 3274.	3.3	7
103	High Performance Ge Devices for Electronic-Photonic Integrated Circuits. ECS Transactions, 2008, 16, 575-582.	0.5	6
104	Effect of a breather soliton in Kerr frequency combs on optical communication systems. Optics Letters, 2016, 41, 1764.	3.3	6
105	Direct bandgap photoluminescence from n-type indirect GaInP alloys. Photonics Research, 2017, 5, 239.	7.0	6
106	Robust generation of frequency combs in a microresonator with strong and narrowband loss. Photonics Research, 2017, 5, 552.	7.0	6
107	Improved retention of phosphorus donors in germanium using a non-amorphizing fluorine co-implantation technique. Journal of Applied Physics, 2018, 123, 161524.	2.5	6
108	Unpredicted Internal Geometric Reconfiguration of an Enclosed Space Formed by Heteroepitaxy. Nano Letters, 2020, 20, 540-545.	9.1	6

JURGEN MICHEL

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109	PIC-integrable, uniformly tensile-strained Ge-on-insulator photodiodes enabled by recessed SiN <sub>x</sub> stressor. Photonics Research, 2021, 9, 1255.	7.0	6
110	Optical characterization of Ge-on-Si laser gain media. , 2011, , .		5
111	Germanium-on-insulator virtual substrate for InGaP epitaxy. Materials Science in Semiconductor Processing, 2017, 58, 15-21.	4.0	5
112	Performance of AlGaInP LEDs on silicon substrates through low threading dislocation density (TDD) germanium buffer layer. Semiconductor Science and Technology, 2018, 33, 104004.	2.0	5
113	Trimming of Athermal Silicon Resonators. , 2012, , .		5
114	Thermo-optical compensation in high-index-contrast waveguides. , 2008, , .		4
115	Solar Spectrum Splitting Parallel Junction High Efficiency Concentrating Photovoltaics. Materials Research Society Symposia Proceedings, 2012, 1391, 46.	0.1	4
116	Extension of Germanium-on-insulator optical absorption edge using CMOS-compatible silicon nitride stressor. , 2017, , .		4
117	Trapping threading dislocations in germanium trenches on silicon wafer. Journal of Crystal Growth, 2020, 543, 125701.	1.5	4
118	A self-aligned dry etching method for mechanical strain enhancement of germanium and its uniformity improvement for photonic applications. , 2018, , .		4
119	Low-cost, Deterministic Quasi-periodic Photonic Structures for light trapping in thin film silicon solar cells. , 2009, , .		3
120	Low-temperature germanium ultra-high vacuum chemical vapor deposition for back-end photonic device integration. , 2010, , .		3
121	Direct demonstration of sensitization at 980nm optical excitation in erbium-ytterbium silicates. , 2010, , .		3
122	Epitaxy and characterization of GaInP/AlInP light-emitting diodes on As-doped Ge/Si substrates. Optics Express, 2016, 24, 23129.	3.4	3
123	Direct MOCVD epitaxy of GaAsP on SiGe virtual substrate without growth of SiGe. Journal of Crystal Growth, 2016, 441, 78-83.	1.5	3
124	Control wafer bow of InGaP on 200 mm Si by strain engineering. Semiconductor Science and Technology, 2017, 32, 125013.	2.0	3
125	High-efficiency normal-incidence vertical p-i-n photodetectors on a germanium-on-insulator platform: publisher's note. Photonics Research, 2018, 6, 46.	7.0	3
126	High Speed Ge Photodetectors on Si Platform for GHz Optical Communications in C+L Bands. Materials Research Society Symposia Proceedings, 2004, 829, 24.	0.1	2

JURGEN MICHEL

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127	Theoretical modeling on hydrogen evolution in ultraviolet light-treated hydrogenated silicon nitride. Journal of Applied Physics, 2008, 104, 094103.	2.5	2
128	Light up the Future of Silicon Microprocessors. ECS Transactions, 2009, 19, 17-28.	0.5	2
129	Optical gain from the direct gap transition of Ge-on-Si at room temperature. , 2009, , .		2
130	Low-temperature germanium ultra-high vacuum chemical vapor deposition for back-end photonic integration. , 2009, , .		2
131	Evanescent Coupling Device Design for Waveguide-Integrated Group IV Photodetectors. Journal of Lightwave Technology, 2010, , .	4.6	2
132	Solar spectral variations and their influence on concentrator solar cell performance. Proceedings of SPIE, 2013, , .	0.8	2
133	Enhanced Self-frequency Shift of Cavity Soliton in Mode-locked Octave-spanning Frequency Comb Generation. , 2014, , .		2
134	Comment on "High Gain Submicrometer Optical Amplifier at Near-Infrared Communication Band― Physical Review Letters, 2016, 117, 219701.	7.8	2
135	Germanium photodetectors on amorphous substrates for electronic-photonic integration. , 2016, , .		2
136	Metalorganic chemical vapor deposition-regrown Ga-rich InGaP films on SiGe virtual substrates for Si-based III-V optoelectronic device applications. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	2.1	2
137	High n-type doped germanium for electrically pumped Ge laser. , 2012, , .		2
138	Broadband athermal waveguides and devices for datacom and telecom applications. , 2018, , .		2
139	Er-doped polycrystalline silicon for light emission at λ=1.54 Âμm. Journal of Electronic Materials, 2000, 29, 973-978.	2.2	1
140	A High Index Contrast Silicon Oxynitride Materials Platform for Er-doped Microphotonic Amplifiers. Materials Research Society Symposia Proceedings, 2004, 817, 42.	0.1	1
141	Ge-based Active Devices for Si Photonics. , 2007, , .		1
142	Monolithic Ge-on-Si lasers for integrated photonics. , 2010, , .		1
143	Ge-on-Si integrated photonics: New tricks from an old semiconductor. , 2010, , .		1
144	Optimization-based design of surface textures for thin-film Si solar cells — Are conventional		1

Lambertian models relevant?., 2011,,.

JURGEN MICHEL

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145	Ge-on-Si lasers for silicon photonics. , 2011, , .		1
146	Electroluminescence of highly doped Ge pnn diodes for Si integrated lasers. , 2011, , .		1
147	A Germanium-on-Silicon Laser for On-chip Applications. , 2011, , .		1
148	Light trapping limits in plasmonic solar cells: an analytical investigation: errata. Optics Express, 2012, 20, 24699.	3.4	1
149	Ge laser and on-chip electronic-photonic integration. , 2012, , .		1
150	Germanium laser: A CMOS compatible light emitter. , 2012, , .		1
151	Electrically Pumped Germanium-on-Silicon Laser. , 2012, , .		1
152	Photodetectors. Series in Optics and Optoelectronics, 2013, , 479-552.	0.0	1
153	Two-cycle pulse generation from mode-locked Kerr frequency combs based on an integrated dispersion-flattened micro-resonator. , 2014, , .		1
154	Micro-Prism Spectrum Splitting Optics for Lateral-Arrayed Multi Junction Micro CPV. , 2019, , .		1
155	Germanium Photodetectors with 60-nm Absorption Coverage Extension and â^1⁄42× Quantum Efficiency Enhancement across L-Band. , 2019, , .		1
156	Amorphous Silicon in Microphotonics. Springer Handbooks, 2019, , 1483-1493.	0.6	1
157	Wavelength-flexible Kerr Frequency Comb Generation Covering a 2000-nm Bandwidth in Mid-Infrared. , 2016, , .		1
158	Band-engineered Ge as gain medium for Si-based laser. , 2008, , .		1
159	Two-octave dispersion flattening with five zero-dispersion wavelengths in the mid-IR. , 2018, , .		1
160	Strained Ge <sub>0.99</sub> Si <sub>0.01</sub> Modulator Arrays for Integrated Broadband Modulation. , 2020, , .		1
161	Engineering Low Dark Current Density for Ge-on-Si Photodiodes. , 2021, , .		1
162	Effect of Crystalization On Photoluminescence of ER2O3 Thin Films. Materials Research Society Symposia Proceedings, 2001, 694, 1.	0.1	0

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163	Ge Photodetectors Integrated with Waveguides for Electronic-Photonic Integrated Circuits on CMOS Platform. , 2007, , .		0
164	High n++ doped germanium: Dopant in-diffusion and modeling. , 2011, , .		0
165	High capacity, photo-trimmable athermal silicon waveguides. , 2012, , .		0
166	Large transient optical gain from N <sup>+</sup> Ge-on-Si. , 2012, , .		0
167	Development of a chip-to-chip optical interconnect system. , 2013, , .		0
168	Theoretical analysis of bulk Ge-on-Si laser performance. , 2013, , .		0
169	Reversed self-steepening in nonlinear pulse propagation along a silicon nano-crystal slot waveguide with engineered dispersion of nonlinearity. , 2013, , .		0
170	High n-Type Doping in Ge for Optical Gain and Lasing. Solid State Phenomena, 2013, 205-206, 394-399.	0.3	0
171	Dispersion-Engineered Silicon Nitride Waveguide for Supercontinuum Generation at Visible Wavelengths. , 2014, , .		0
172	Impact of breather soliton in Kerr combs on the performance of communication systems. , 2015, , .		0
173	Thermally tunable resonator using directly integrated metallic heater. , 2015, , .		0
174	Impact of Higher-Order Dispersion on the Performance of a Kerr Frequency Comb as Affected by the Generated Dispersive Wave. , 2015, , .		0
175	Mid-infrared supercontinuum generation in a low-dispersion Ge-on-Si waveguide using sub-picosecond pulses. , 2016, , .		0
176	Low-loss SOI waveguides at Mid-IR wavelengths (4800 nm) using the second-order TE mode. , 2016, , .		0
177	High quality Ge-OI, III–V-OI on 200 mm Si substrate. , 2016, , .		0
178	Robust generation of Kerr frequency combs with strong and localized spectral loss. , 2016, , .		0
179	Germanium-on-insulator virtual substrate for InGaP epitaxy. Materials Science in Semiconductor Processing, 2017, 70, 17-23.	4.0	0
180	Germanium Photodetector with Enhanced Photo-Response at the L-Band and Beyond for Integrated Photonic Applications. , 2018, , .		0

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181	Germanium Photodetectors with 60-nm Absorption Coverage Extension and â^1⁄42× Quantum Efficiency Enhancement across L-Band. , 2019, , .		0
182	Integrated GeSi Electro-Absorption Modulators on SOI. , 2008, , .		0
183	A Ge-on-Si Laser for Electronic-Photonic Integration. , 2009, , .		0
184	Active Ge Based Devices for Silicon Photonics. , 2009, , .		0
185	Monolithic Ge-on-Si lasers. , 2010, , .		0
186	Germanium on Silicon Lasers and Detectors. , 2011, , .		0
187	High n-type Doping for Ge Lasers. , 2011, , .		0
188	The Ge-on-Si Integrated Microphotonic Platform. , 2013, , .		0
189	Raman scattering and Kerr shock induced breather soliton in Kerr frequency comb generation. , 2015, , $\cdot$		0
190	Mid-IR Kerr Frequency Comb Generation from 4000 to 10000 nm in a CMOS-compatible Germanium Microcavity. , 2016, , .		0
191	Agile generation of microresonator-based frequency combs without pump detuning and local temperature controlling. , 2018, , .		0
192	Uniformly Tensile-strained Germanium Enabled by a Recessed Nitride Stressor for Efficient Integrated Photodetectors at Longer Wavelengths. , 2019, , .		0